Complementary Silicon High-Power Transistors

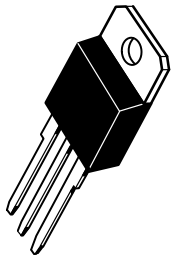
. . . for general–purpose power amplifier and switching applications.

- 10 A Collector Current
- Low Leakage Current — I_{CEO} = 0.7 mA @ 60 V
- Excellent dc Gain — h_{FE} = 40 Typ @ 3.0 A
- High Current Gain Bandwidth Product — h_{fe} = 3.0 min @ I_C = 0.5 A, f = 1.0 MHz

NPN
TIP33B*
TIP33C
PNP
TIP34B*
TIP34C

***Motorola Preferred Device**

10 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS 100 VOLTS 80 WATTS



CASE 340D–01
TO–218AC

MAXIMUM RATINGS

Rating	Symbol	TIP33B TIP34B	TIP33C TIP34C	Unit
Collector–Emitter Voltage	V_{CEO}	80 V	100 V	Vdc
Collector–Base Voltage	V_{CB}	80 V	100 V	Vdc
Emitter–Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous Peak (1)	I_C	10 15		Adc
Base Current — Continuous	I_B	3.0		Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 80 0.64		 Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.56	°C/W
Junction–To–Free–Air Thermal Resistance	$R_{\theta JA}$	35.7	°C/W

(1) Pulse Test: Pulse Width = 10 ms, Duty Cycle ≤ 10%.

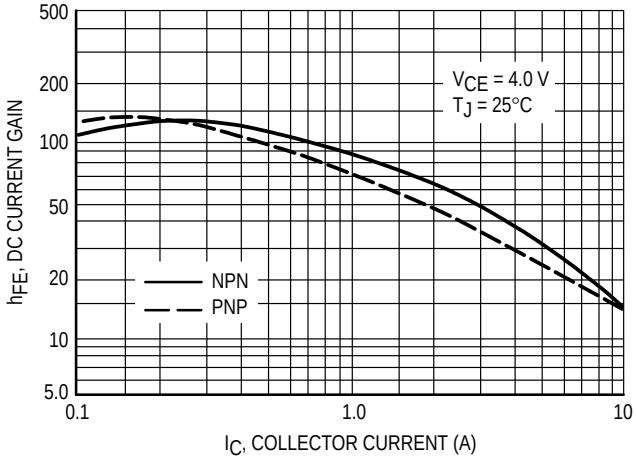


Figure 1. DC Current Gain

Preferred devices are Motorola recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I_C = 30 mA, I_B = 0)	TIP33B, TIP34B TIP33C, TIP34C	$V_{CEO(sus)}$	 80 100	 — —	Vdc
Collector–Emitter Cutoff Current (V_{CE} = 60 V, I_B = 0)	TIP33B, TIP33C, TIP34B, TIP34C	I_{CEO}	—	0.7	mA
Collector–Emitter Cutoff Current (V_{CE} = Rated V_{CEO}, V_{EB} = 0)		I_{CES}	—	0.4	mA
Emitter–Base Cutoff Current (V_{EB} = 5.0 V, I_C = 0)		I_{EBO}	—	1.0	mA
ON CHARACTERISTICS (1)					
DC Current Gain (I_C = 1.0 A, V_{CE} = 4.0 V) (I_C = 3.0 A, V_{CE} = 4.0 V)		h_{FE}	 40 20	 — 100	—
Collector–Emitter Saturation Voltage (I_C = 3.0 A, I_B = 0.3 A) (I_C = 10 A, I_B = 2.5 A)		$V_{CE(sat)}$	 — —	 1.0 4.0	Vdc
Base–Emitter On Voltage (I_C = 3.0 A, V_{CE} = 4.0 V) (I_C = 10 A, V_{CE} = 4.0 V)		$V_{BE(on)}$	 — —	 1.6 3.0	Vdc
DYNAMIC CHARACTERISTICS					
Small–Signal Current Gain (I_C = 0.5 A, V_{CE} = 10 V, f = 1.0 kHz)		h_{fe}	20	—	—
Current–Gain — Bandwidth Product (I_C = 0.5 A, V_{CE} = 10 V, f = 1.0 MHz)		f_T	3.0	—	MHz

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

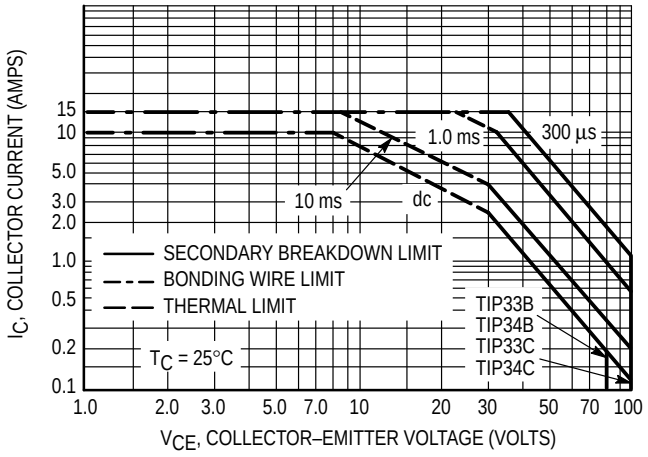


Figure 2. Maximum Rated Forward Bias Safe Operating Area

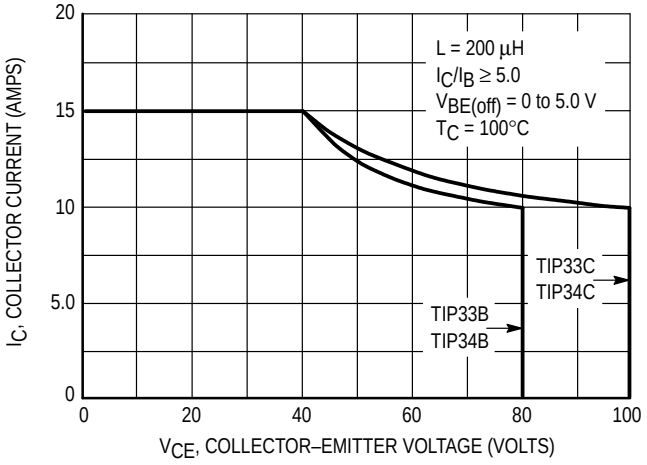


Figure 3. Maximum Rated Forward Bias Safe Operating Area

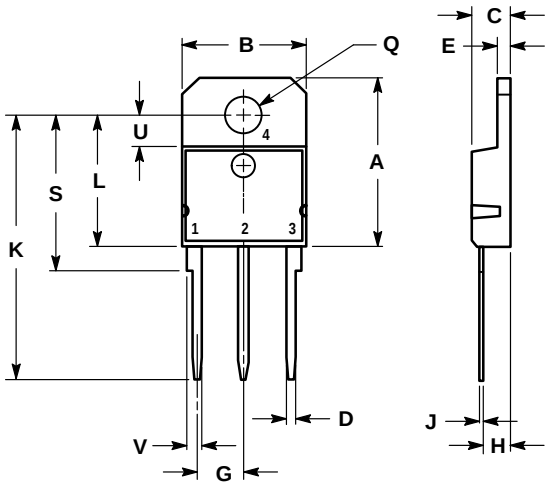
FORWARD BIAS

The Forward Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during forward bias. The data is based on T_C = 25°C; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10%, and must be derated thermally for T_C > 25°C.

REVERSE BIAS

The Reverse Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during reverse biased turn–off. This rating is verified under clamped conditions so the device is never subjected to an avalanche mode.

PACKAGE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	19.00	19.60	0.749	0.771
B	14.00	14.50	0.551	0.570
C	4.20	4.70	0.165	0.185
D	1.00	1.30	0.040	0.051
E	1.45	1.65	0.058	0.064
G	5.21	5.72	0.206	0.225
H	2.60	3.00	0.103	0.118
J	0.40	0.60	0.016	0.023
K	28.50	32.00	1.123	1.259
L	14.70	15.30	0.579	0.602
Q	4.00	4.25	0.158	0.167
S	17.50	18.10	0.689	0.712
U	3.40	3.80	0.134	0.149
V	1.50	2.00	0.060	0.078

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

CASE 340D–01
TO–218AC
ISSUE A

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